

Complementary techniques to investigate degradation mechanisms in solar cells

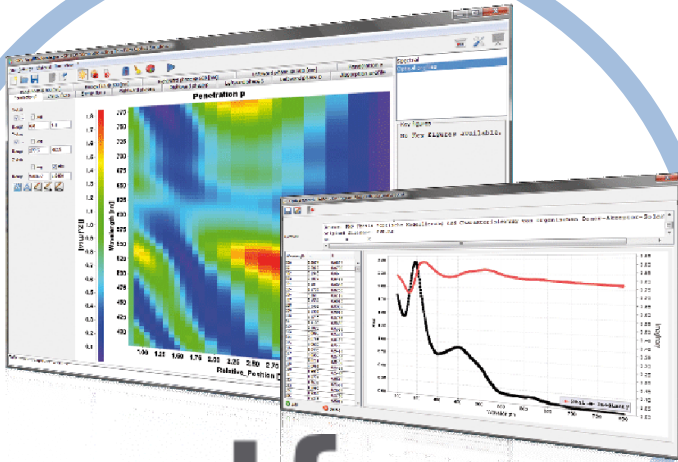
Simon Züfle^{a,b}, Martin Neukom^a, Beat Ruhstaller^{a,b}

a: Fluxim AG, Winterthur, Switzerland

b: Institute of Computational Physics, ZHAW, Winterthur, Switzerland

Who we are

Simulation Software



setfos



swiss made
software

Research on
OLED and OPV



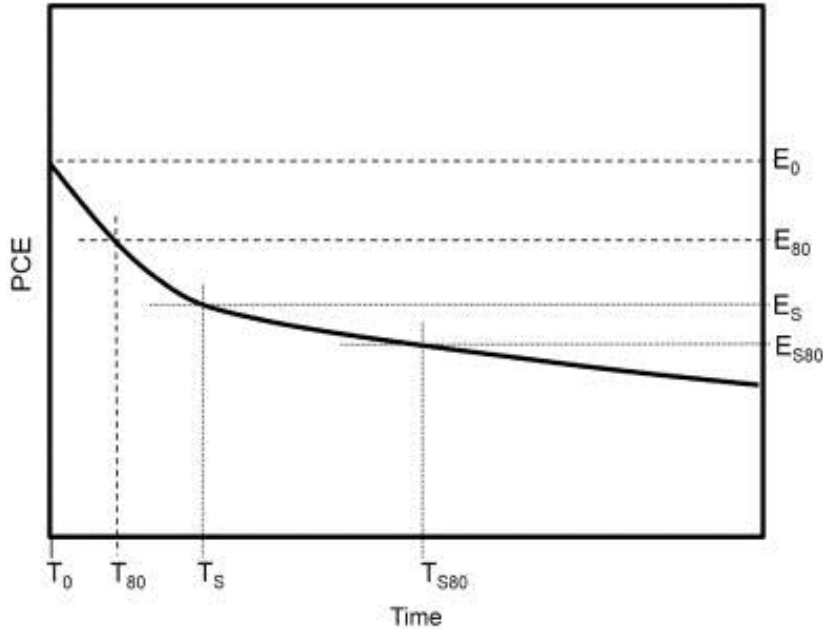
Sunflower



paios

Measurement Hardware

Stability of Solar Cells



How to characterize and compare stability?

→ Standardization!

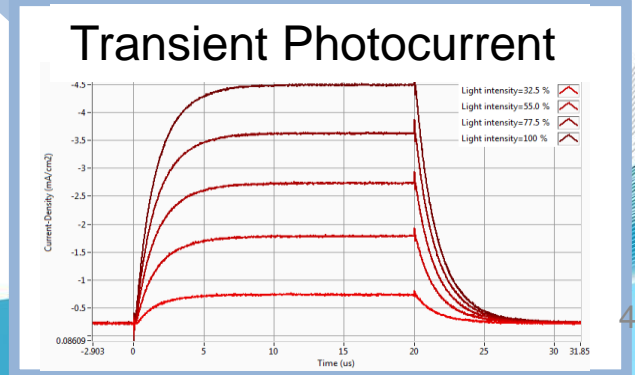
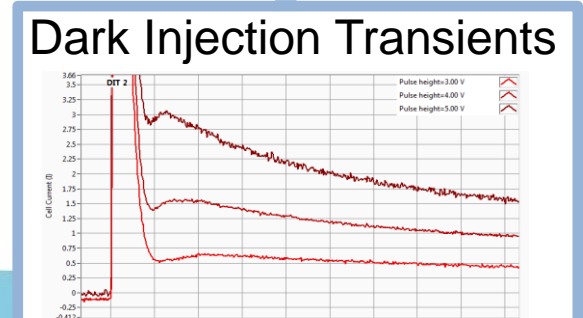
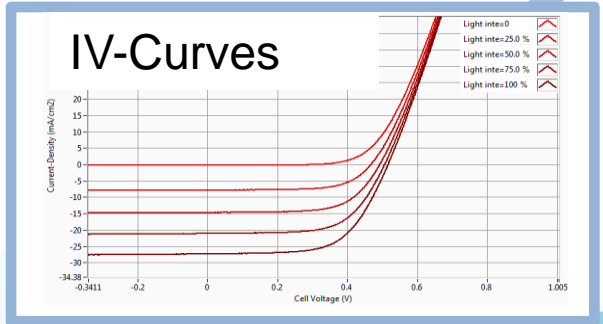
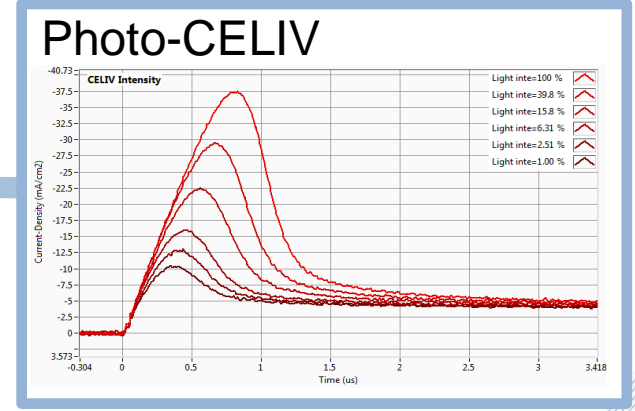
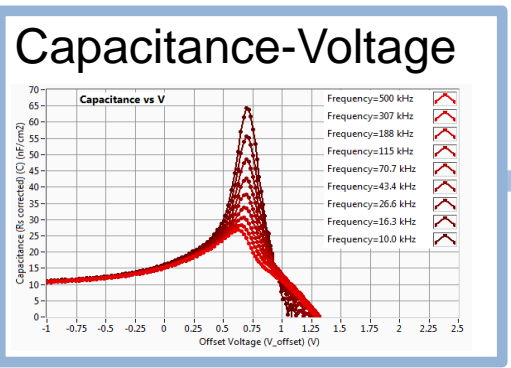
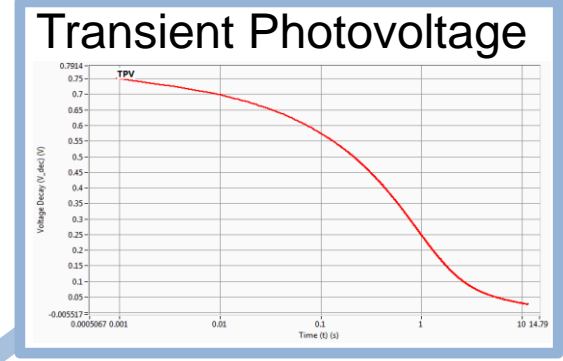
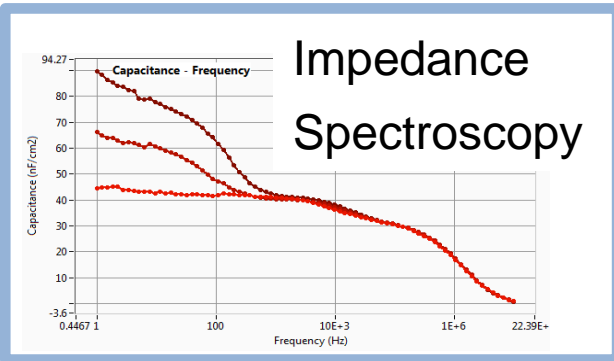
- IEC 61215 for c-Si
- IEC 61646 for thin-film
- ISOS Protocols for OPV

Reese et al., Solar Energy Materials and Solar Cells, (2011), 95, 1253

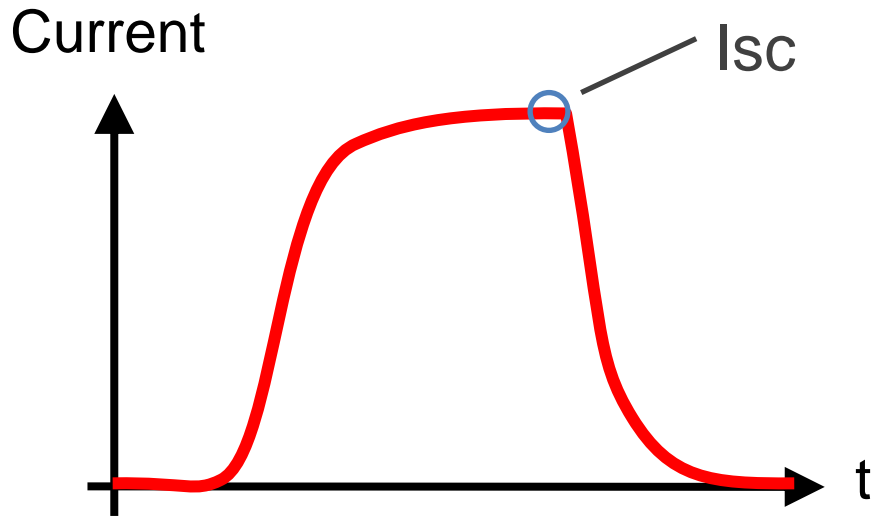
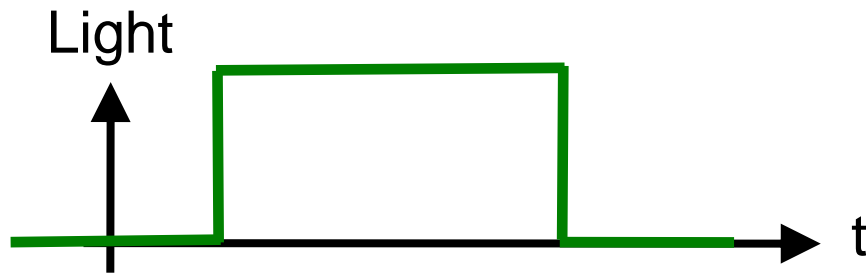
But: focussed on steady-state, where valuable information on degradation is concealed.



Techniques we propose:

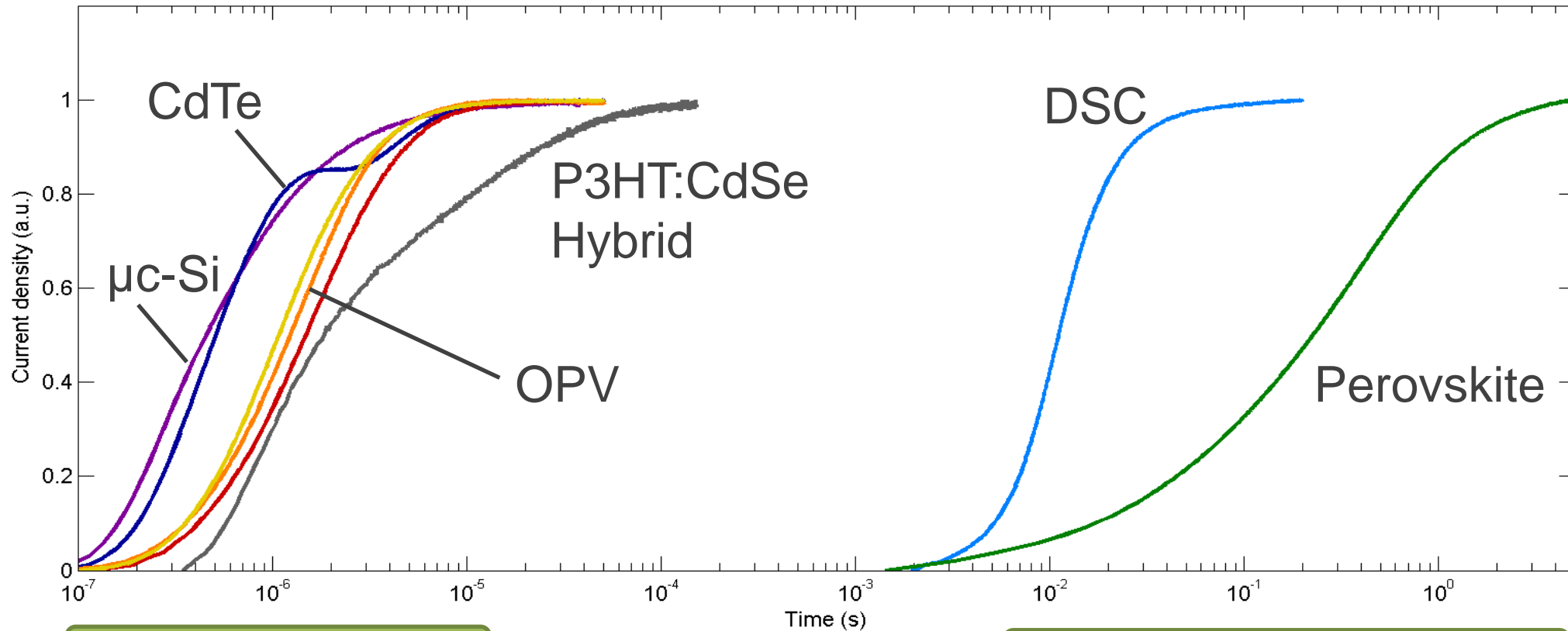


Transient Photocurrent TPC



- Cell is flashed at constant voltage
- Qualitative investigation of charge **carrier mobility**
- Qualitative investigation of **trapping dynamics**

Transient Photocurrent: Technology Comparison



Drift & Diffusion

Ionic movement

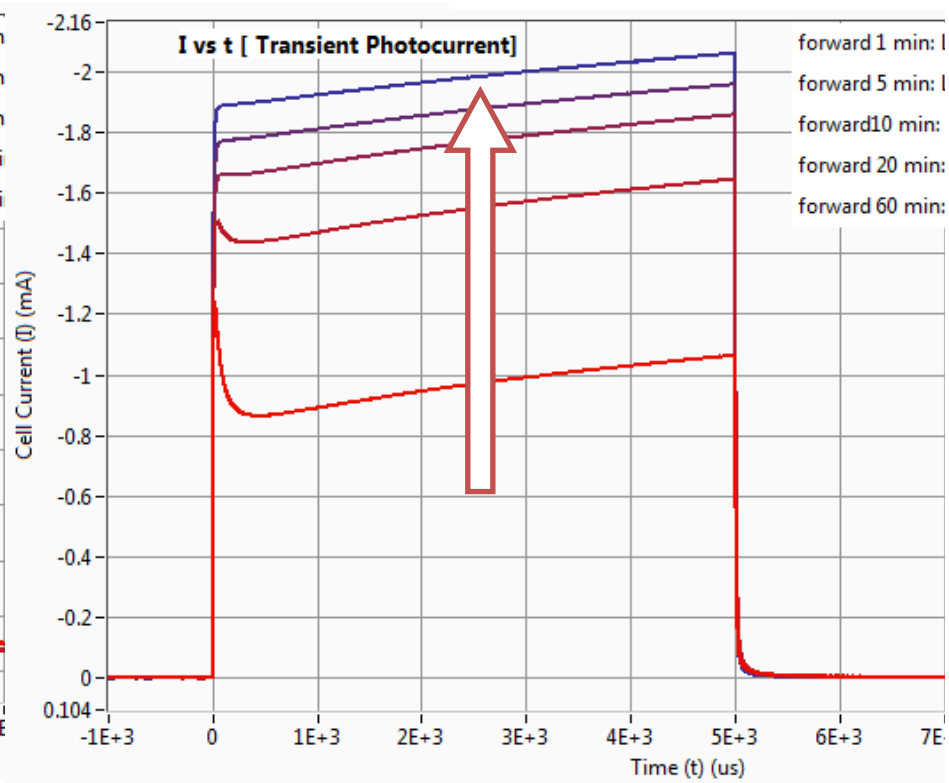
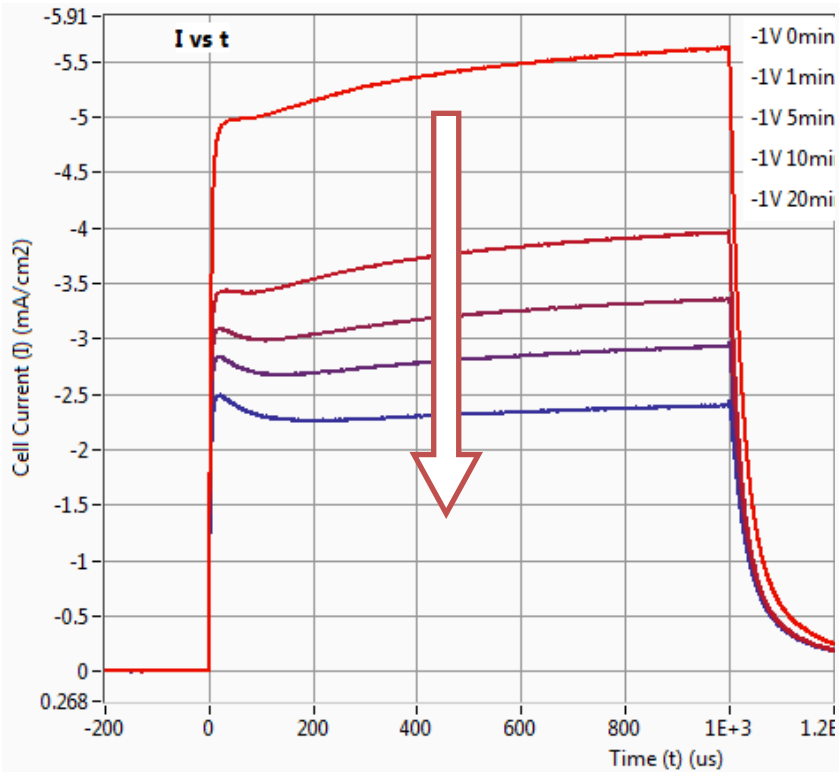
Traps

Other slow effect?

Space-charge effects due to doping

Stress-Test Module

Repeated Transient Photocurrent on Perovskite SC



Preconditioning -1V

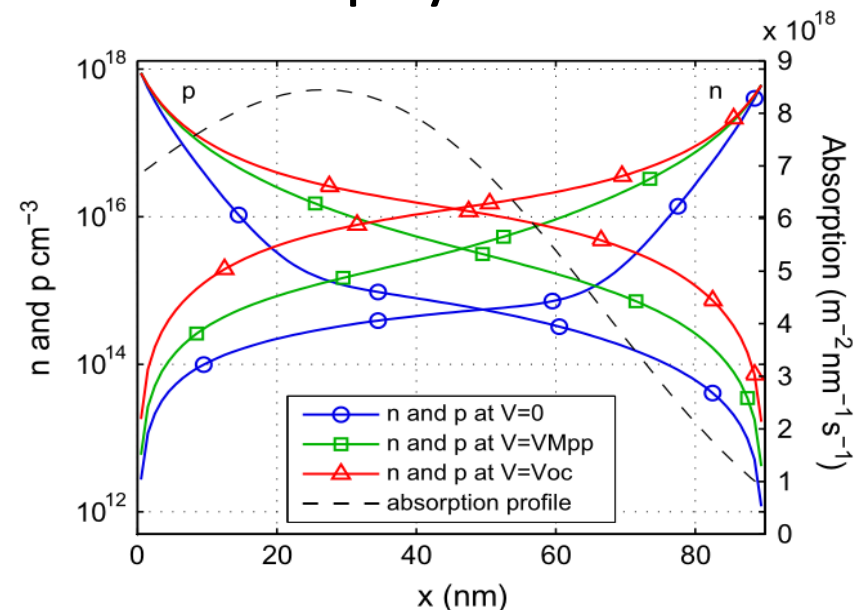
Preconditioning +1V

→ Evidence for movement of ionic charges

Modeling

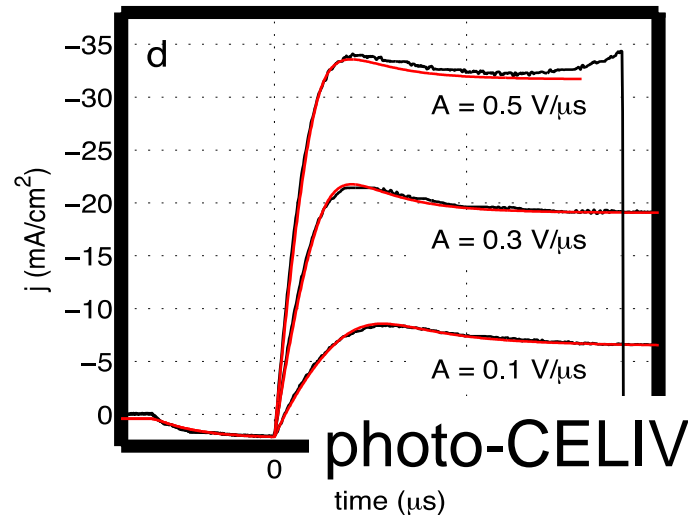
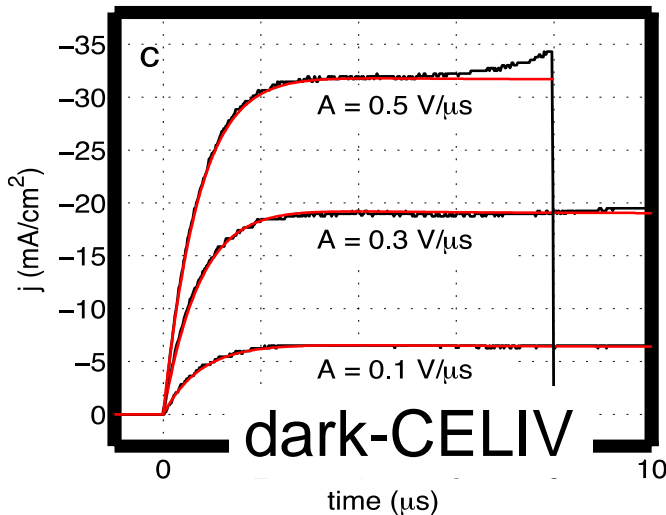
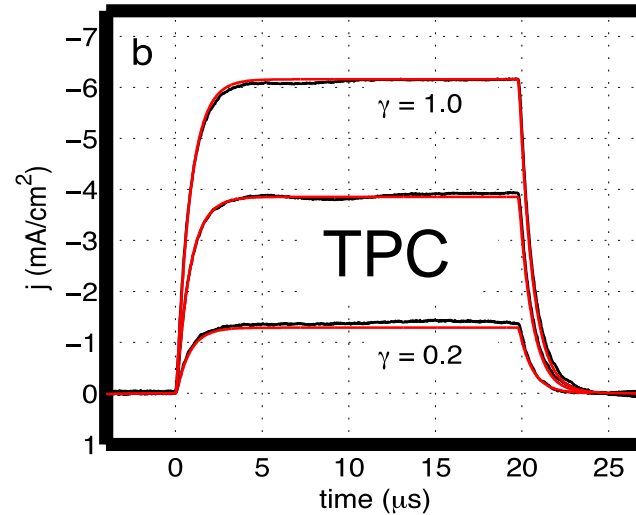
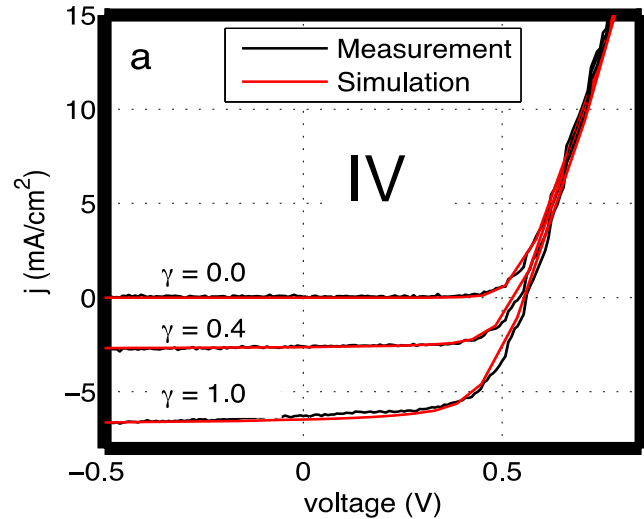
- Drift-Diffusion Simulation
- Simulate all experiments with one set of parameters
- Modeling helps to understand device physics
- Get further insight into device

setfos
semiconducting thin film optics simulation software



Neukom et al.,
Org. El. 13,2910 (2012)

Advanced Characterization Example



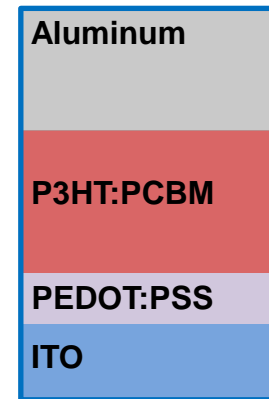
Measurement and simulation of an organic solar cell

Global fit with one set of parameters!

Neukom et al.,
Org. El. 13,2910 (2012)

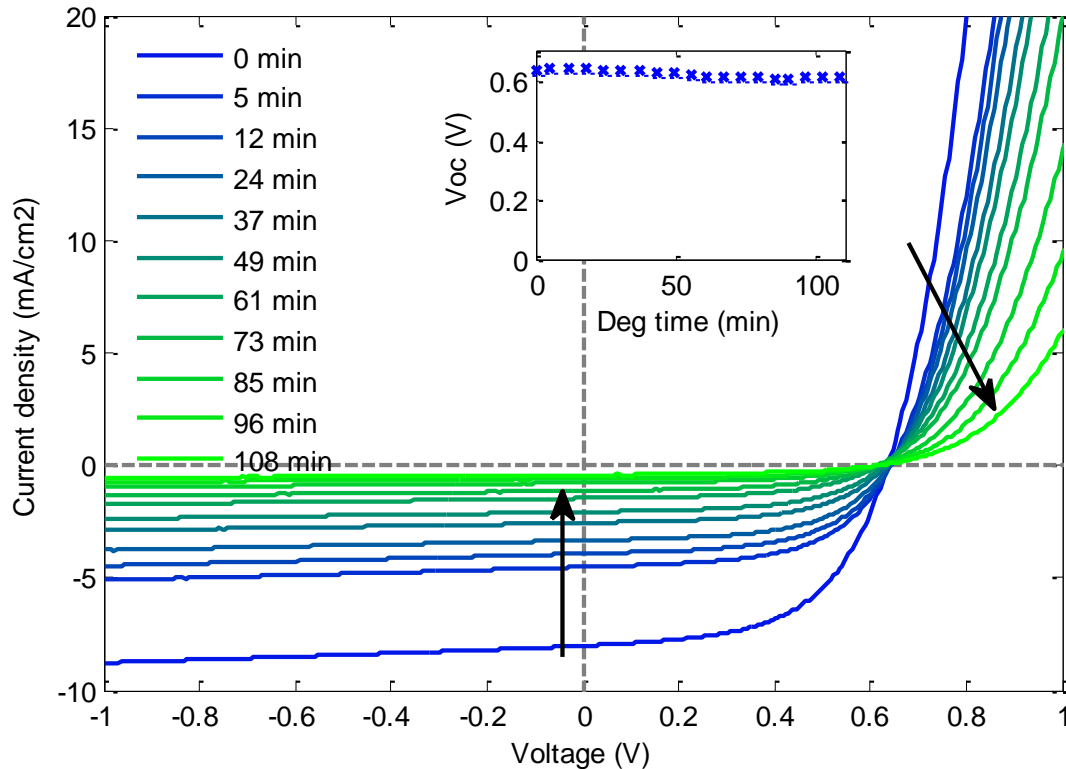
Accelerated Ageing Study

- Standard unencapsulated P3HT:PCBM organic solar cells with PEDOT:PSS as hole transport layer (unstable)
- In climate chamber at 45°C, 85%RH
→ investigate influence of humidity
- Automated repetition of measurement routine
→ Highly systematic data!

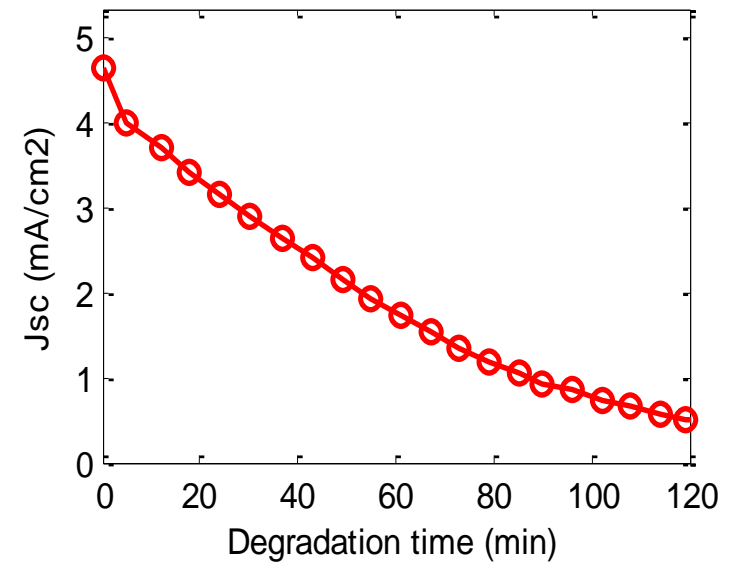


Steady-State Measurements

Current-Voltage

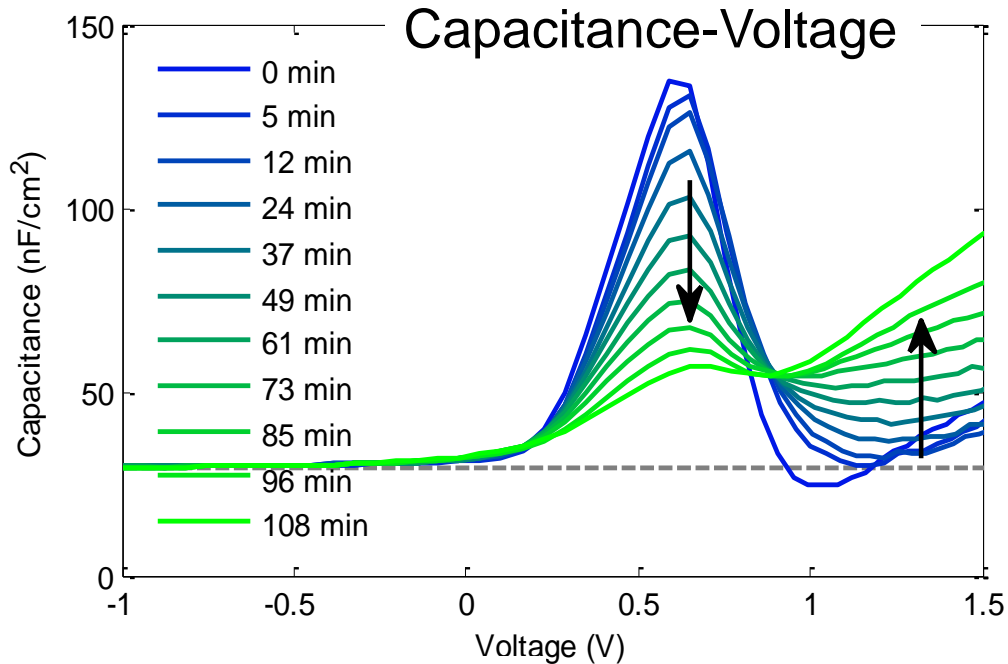


Short-circuit current



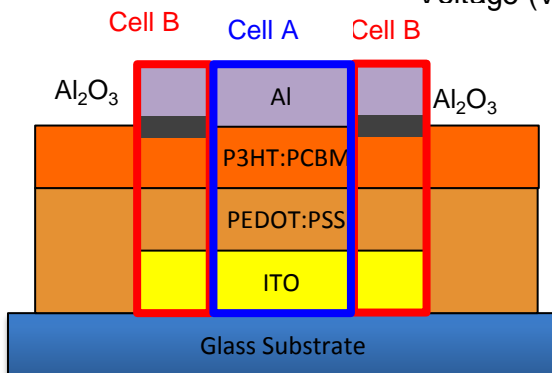
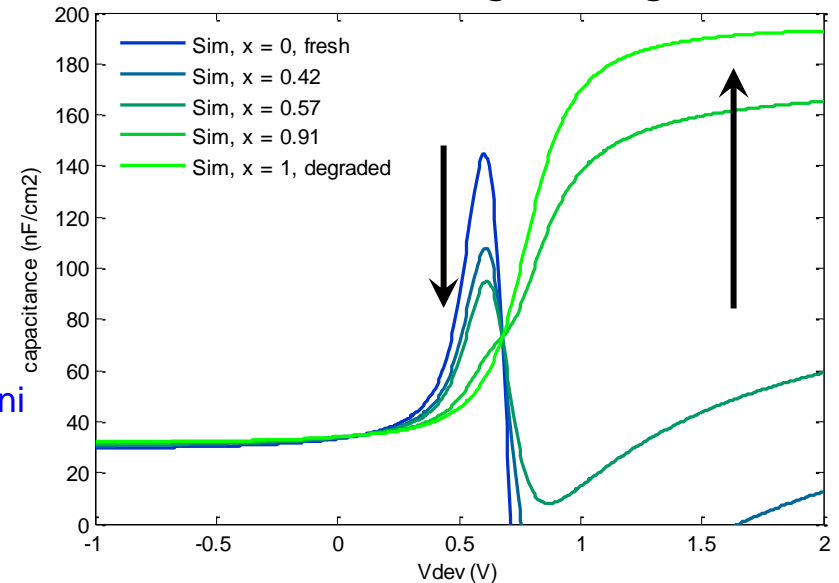
No conclusions about degradation mechanism possible!

AC Measurements



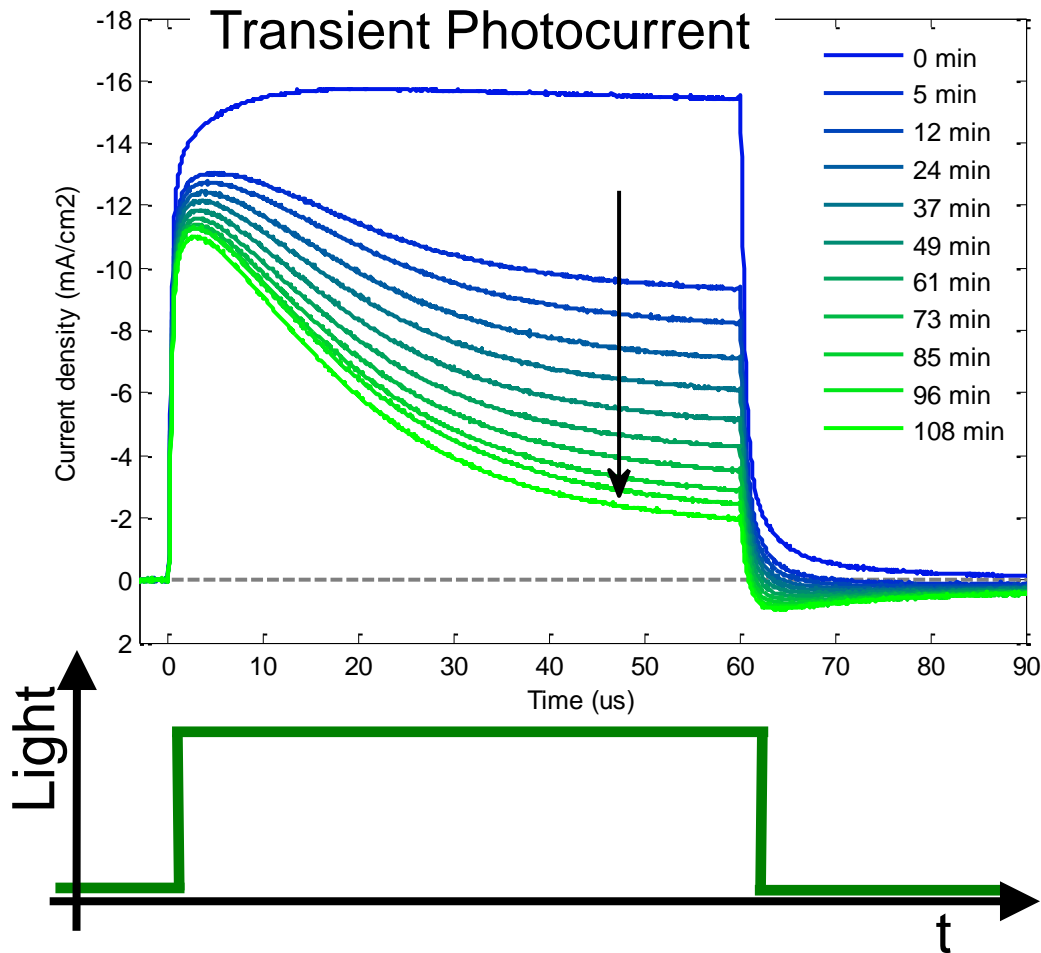
Hypothesis: Insulating Al₂O₃ interface layer grows, leading to MIS structure.

Simulation of growing MIS



Surface A: $(1-x) \cdot S_{ini}$
Surface B: $(x) \cdot S_{ini}$

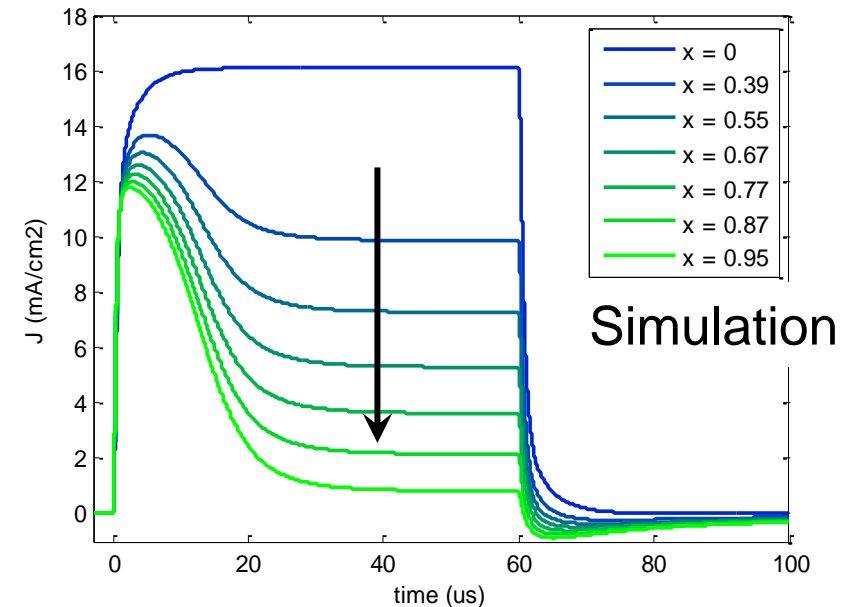
Transient Measurements



«There is life after death!»

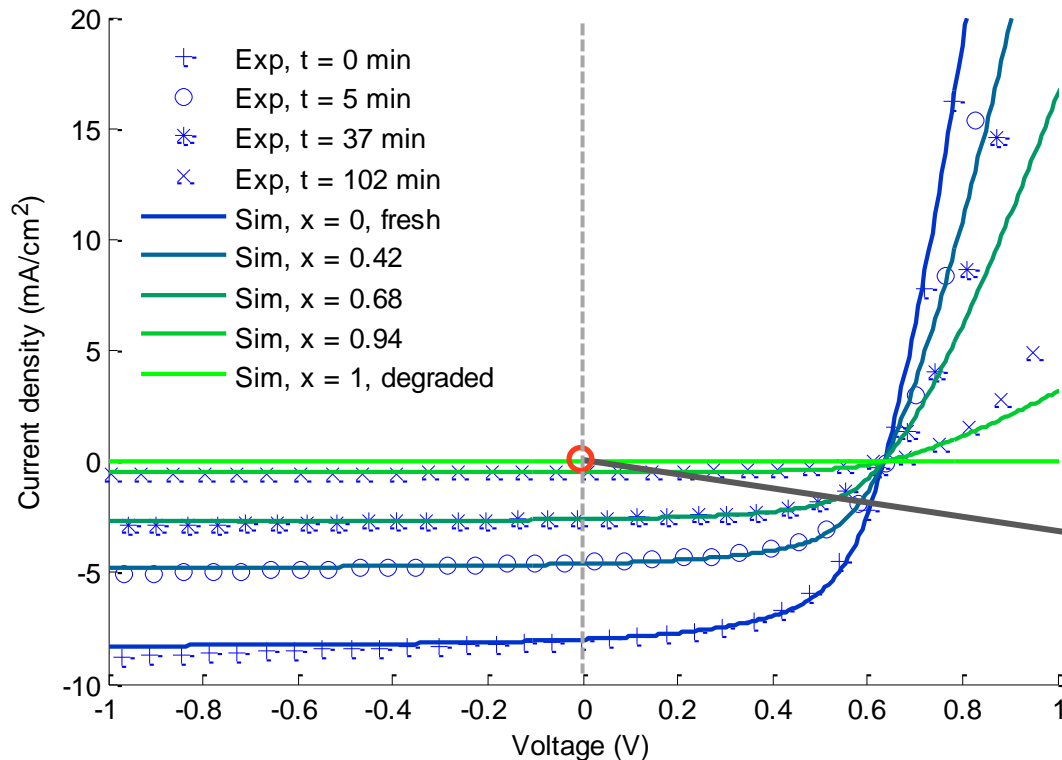
Charge extraction is hindered:

→ Blocking Al₂O₃ layer

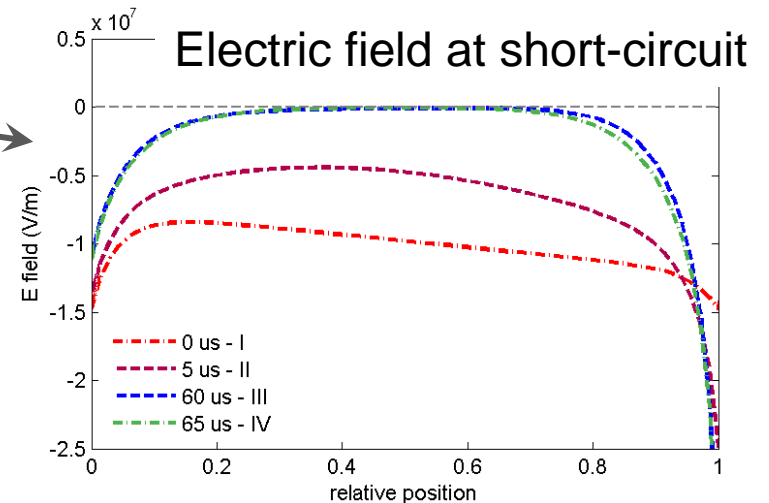


Comparison

IV: Paios Measurements + Setfos Simulations



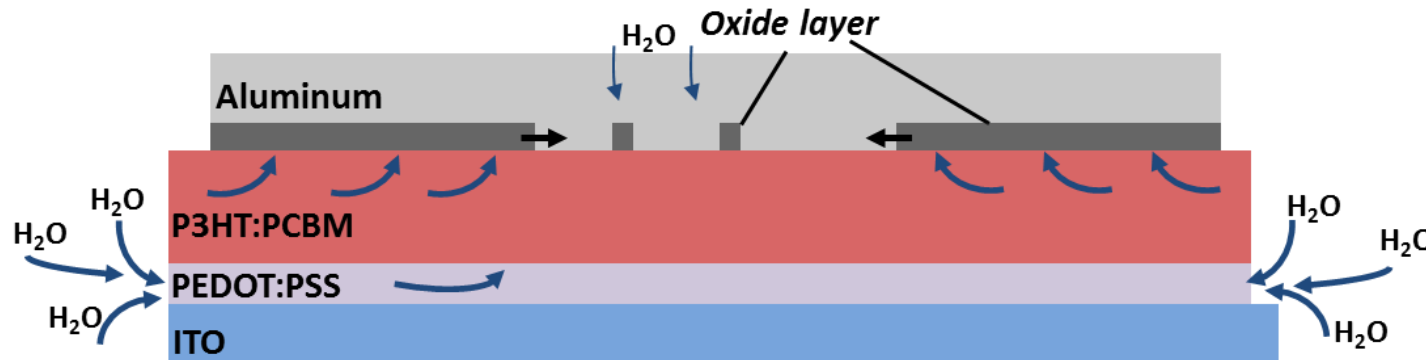
Model-based analysis helps to quantitatively validate the postulated degradation mechanism!



x describes effective area vs time, in agreement with a 2D diffusion model

Conclusions

- Hypothesis: Al_2O_3 layer acts as insulating interface resulting in a **local** complete loss of current



→ **Lateral** instead of homogeneous degradation process!

This conclusion is possible without time-consuming, expensive and destructive methods!

Züfle et al., Adv. En. Mater., 2015, in press, 10.1002/aenm.201500835

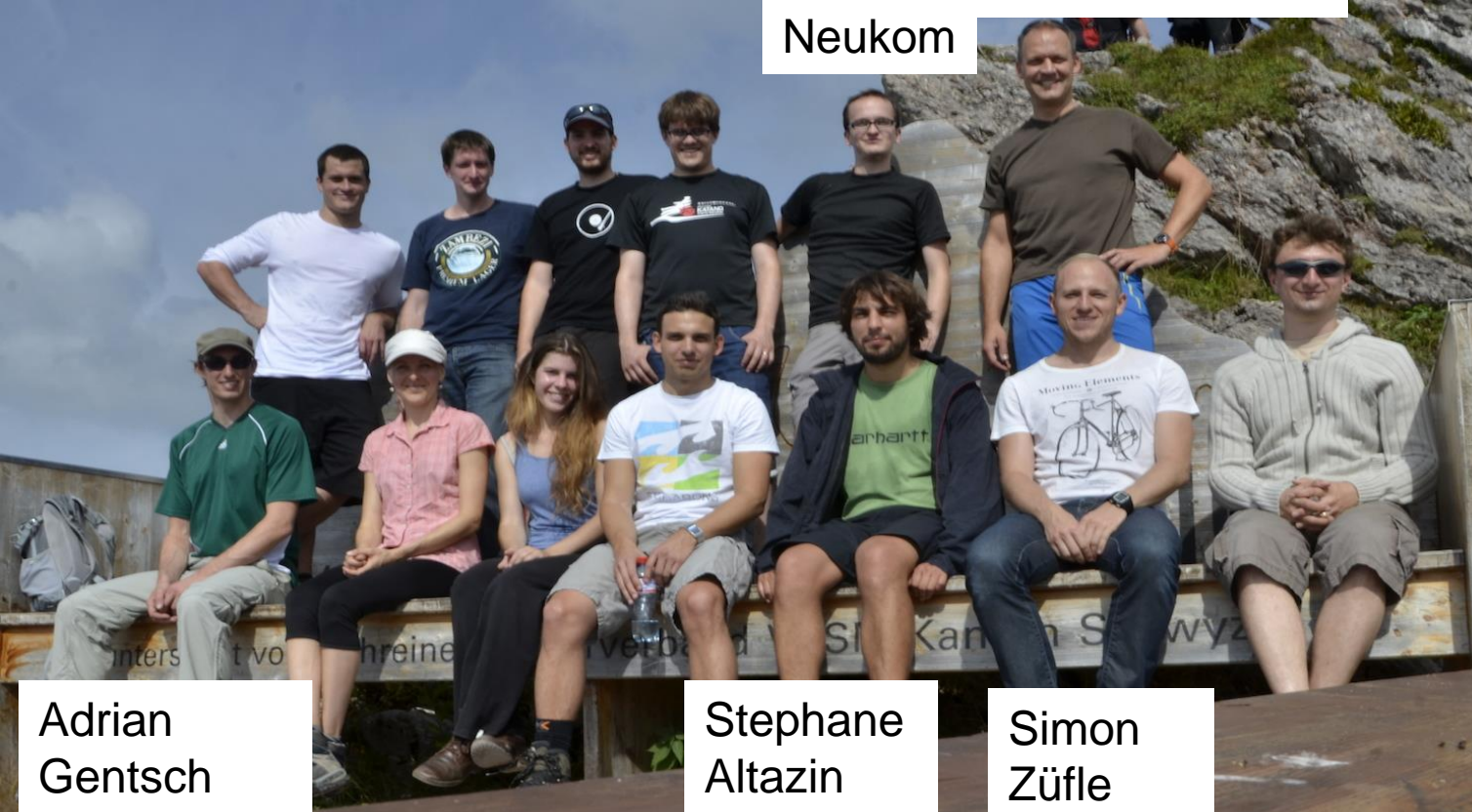
Summary

- IV-curves alone are not enough to understand degradation processes
- Transient and impedance techniques reveal valuable information
- Systematic measurement data allows for combinatorial analysis
- Advanced Modeling helps to validate hypothesis and gives additional insight into the device

Acknowledgement

Martin
Neukom

Beat Ruhstaller



Adrian
Gentsch

Stephane
Altazin

Simon
Züfle

Zurich University
of Applied Sciences

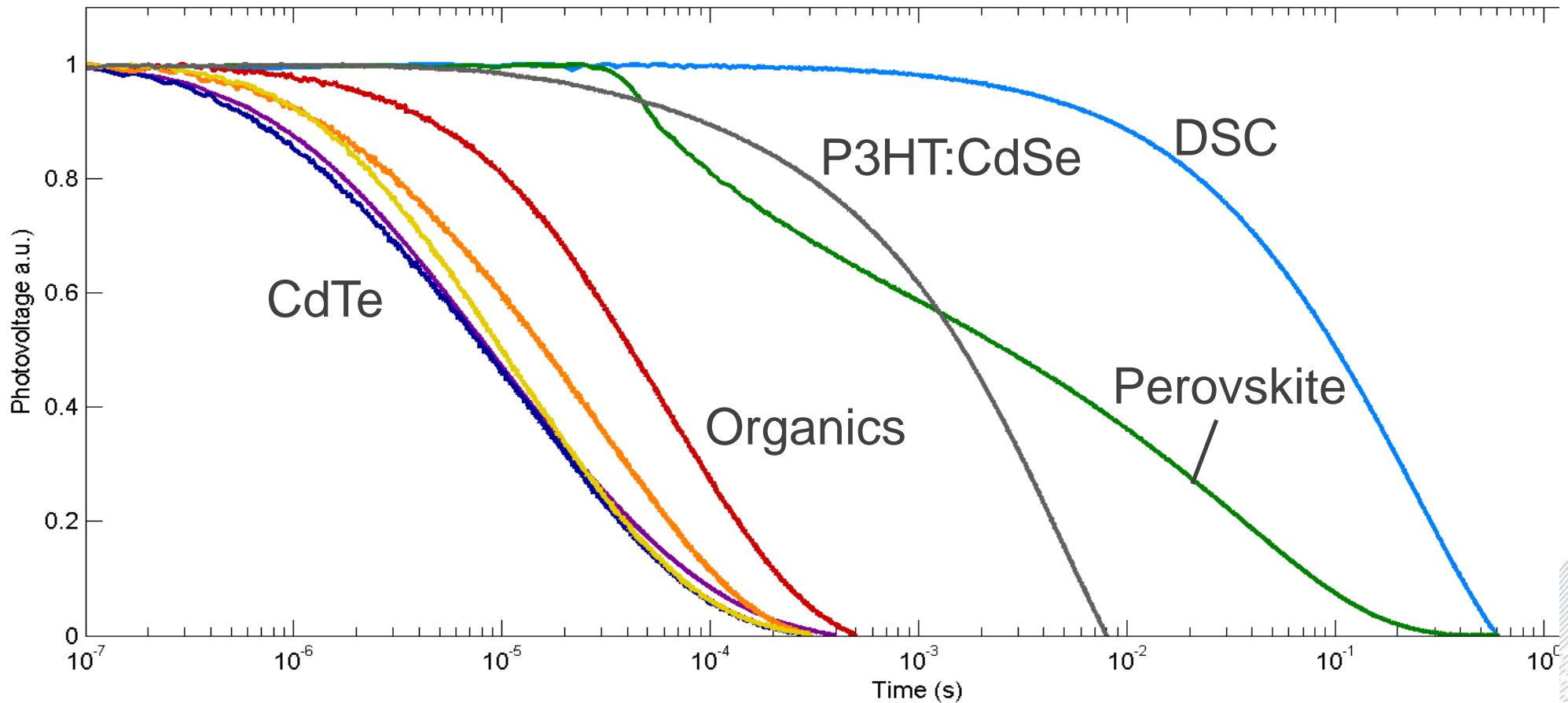
zhaw School of
Engineering
ICP Institute of
Computational Physics

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Thank you for your attention!

Transient Photovoltage



Recombination

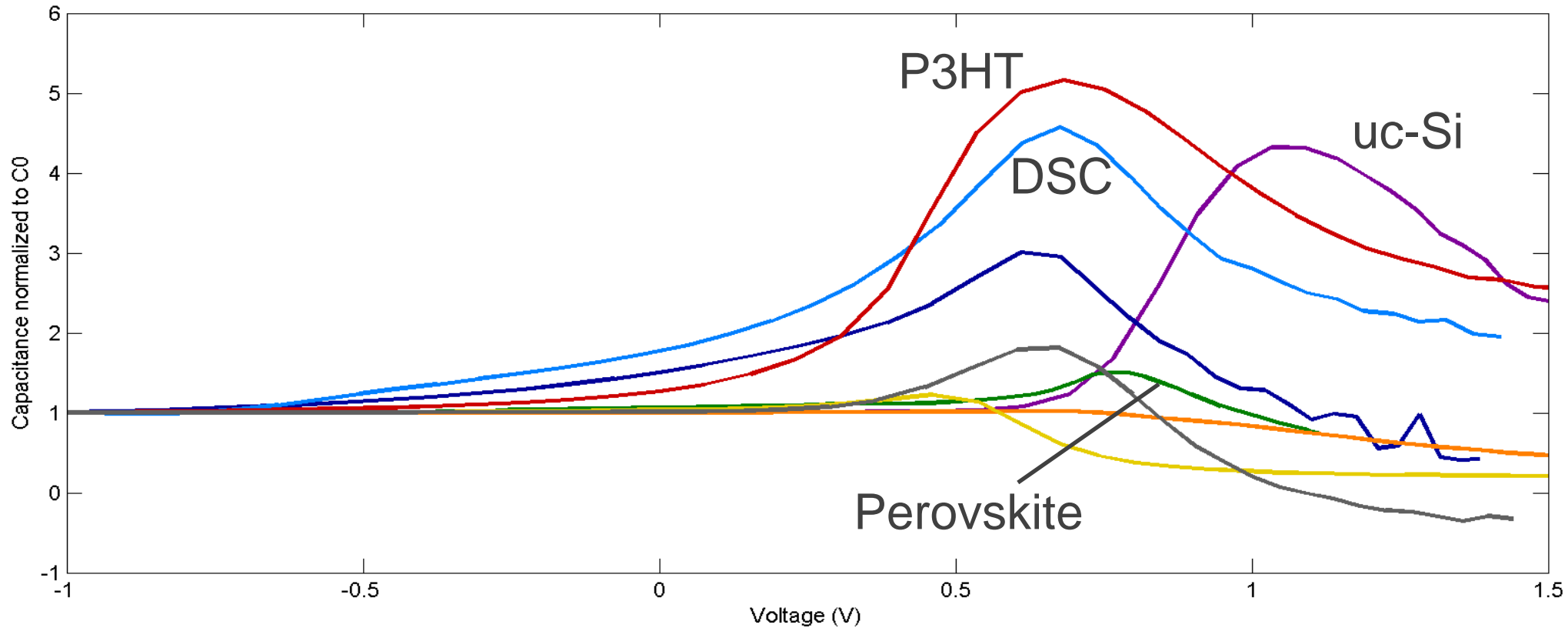
Drift & Diffusion

Traps

Ions?

Leakage Current

Capacitance-Voltage



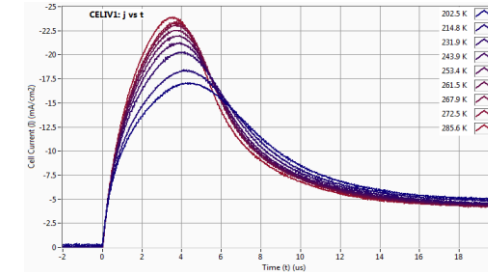
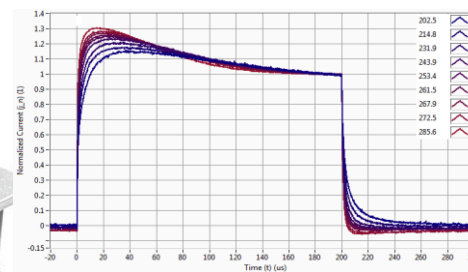
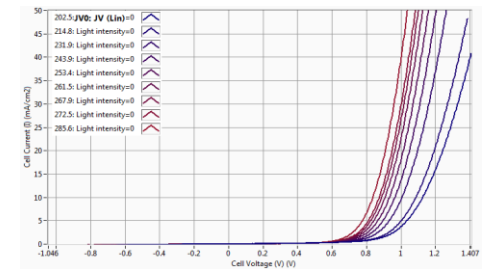
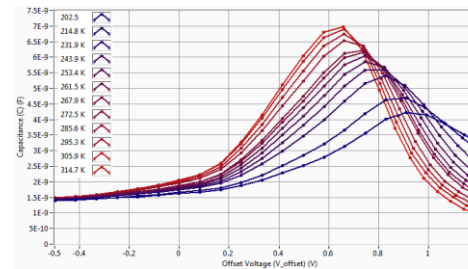
Doping

Injection barriers

Built-in voltage

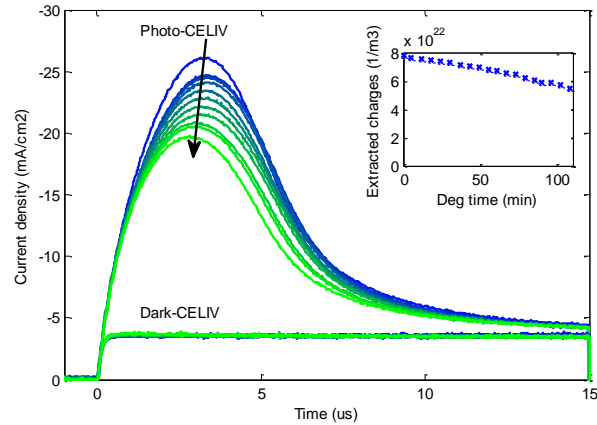
Low Temperature Module

Perform all experiments at temperatures from **150 to 350 K**

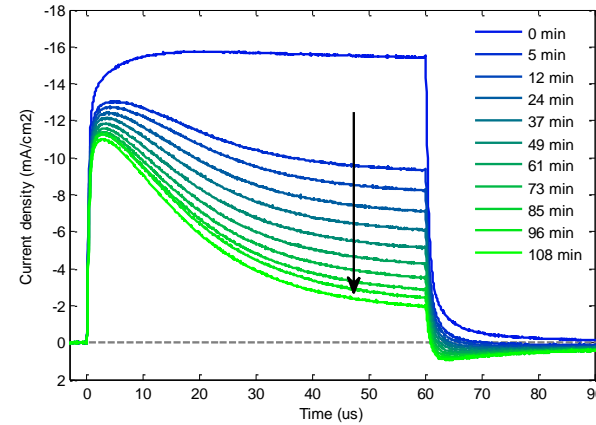


Transient and ac Measurements

CELIV

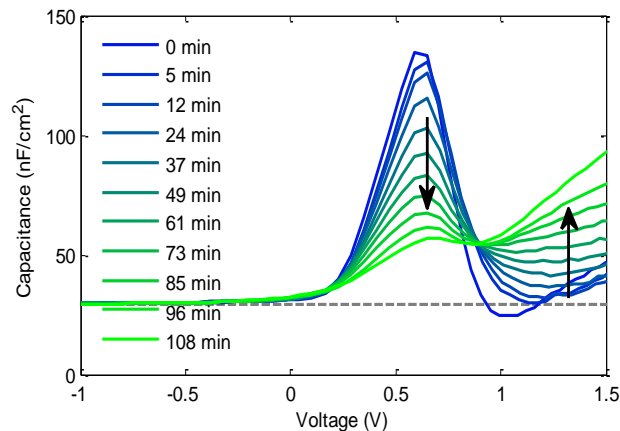


TPC

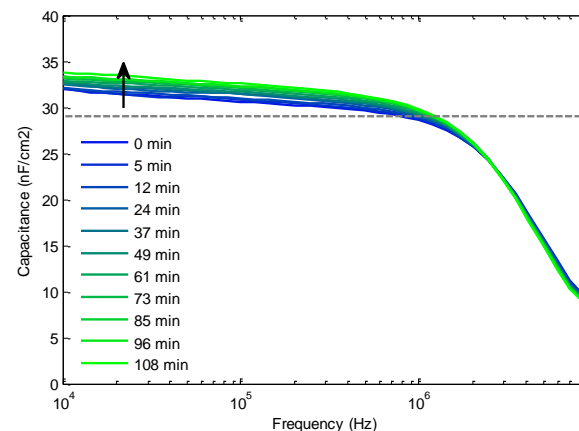


Systematic data of the same device during degradation!

C-V



C-f



Combinatorial Analysis

- Electrode workfunctions are constant
 - Electrode resistance is constant
 - Layer thickness is constant
 - No doping is present
 - Traps cannot be dominant mechanism
 - Absorption loss cannot be dominant mechanism
 - Decreased mobility cannot be dominant mechanism
 - Space charge due to hampered extraction
- There is life even in dead cells!